

S20T150FB

SCHOTTKY BARRIER

RECTIFIERS

20 AMPERES

150 VOLTS

Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Refractory metal capable of high temperature operation metal. The proprietary barrier technology allows for reliable operation up to 150° C junction temperature. Typical application are in switching Mode Power Supplies such as adaptors, DC/DC converters, free-wheeling and polarity protection diodes.

Features

- *Low Forward Voltage.
- *Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- * Low Power Loss & High efficiency.
- *175℃ Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory
- Flammability Classification 94V-O

* In compliance with EU RoHs 2002/95/EC directives

MAXIMUM RATINGS

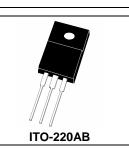
Characteristic	Symbol	S20T150FB	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	150	V
RMS Reverse Voltage	V _{R(RMS)}	105	V
Average Rectifier Forward Current $(per diode)$ Total Device (Rated V _R),	I _{F(AV)}	10 20	A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	250	A
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

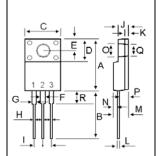
THERMAL RESISTANCES

Typical Thermal Resistance junction to case (per device)	$R_{ extsf{ heta}_{jc}}$	3.6	°C/w
--	--------------------------	-----	------

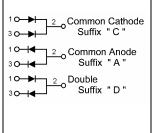
ELECTRIAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур.	Max	Unit
Maximum Instantaneous Forward Voltage (per diode)					
(I _F =0.1 Amp T _C = 25℃)	N/		0.38	0.40	V
(I _F =5.0 Amp T _C = 25℃)	VF		0.70	0.72	V
(I _F =10 Amp T _C = 25℃)			0.77	0.80	
Maximum Instantaneous Reverse Current					
(Rated DC Voltage, $T_c = 25^{\circ}C$)	I _R		0.003	0.01	mA
(Rated DC Voltage, $T_C = 125^{\circ}C$)			5	7	





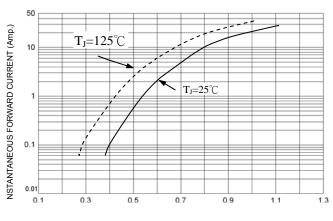
DIM MIN MAX A 15.05 15.15 B 13.35 13.45 C 10.00 10.10 D 6.55 6.65 E 2.65 2.75 F 1.55 1.65 G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20 K 1.10 1.20	
B 13.35 13.45 C 10.00 10.10 D 6.55 6.65 E 2.65 2.75 F 1.55 1.65 G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	DIM
C 10.00 10.10 D 6.55 6.65 E 2.65 2.75 F 1.55 1.65 G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	А
D 6.55 6.65 E 2.65 2.75 F 1.55 1.65 G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	В
E 2.65 2.75 F 1.55 1.65 G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	С
F 1.55 1.65 G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	D
G 1.15 1.25 H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	Е
H 0.55 0.65 I 2.50 2.60 J 3.00 3.20	F
I 2.50 2.60 J 3.00 3.20	G
J 3.00 3.20	н
	1
K 110 120	J
R 1.10 1.20	К
L 0.55 0.65	L
M 4.40 4.60	М
N 1.15 1.25	Ν
O 3.35 3.45	0
P 2.65 2.75	Р
Q 3.15 3.25	Q
R 3.60 3.80	R



S20T150FB

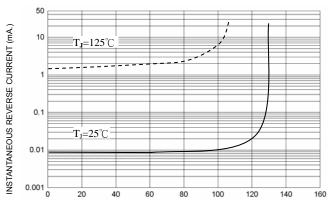
FIG-1 FORWARD CURRENT DERATING CURVE

FIG-2 TYPICAL FORWARD CHARACTERISITICS

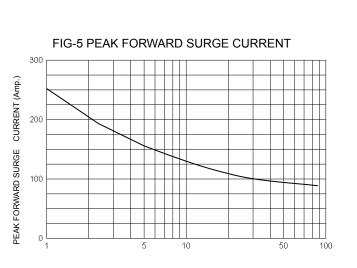


FORWARD VOLTAGE (Volts)

FIG-3 TYPICAL REVERSE CHARACTERISTICS

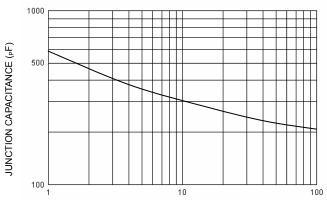


PERCENT OF RATED REVERSE VOLTAGE (%)



NUMBER OF CYCLES AT 60 Hz

FIG-4 TYPICAL JUNCTION CAPACITANCE



PERCENT OF RATED REVERSE VOLTAGE (%)